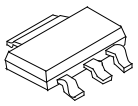
2SK3476

Preliminary ***POWER MOSFET***

FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOSFET TYPE, VHF/UHF BAND AMPLIFIER APPLICATIONS



SOT-223

■ DESCRIPTION

The UTC **2SK3476** are intended for high frequency Power Amplifier of telecommunications equipment.

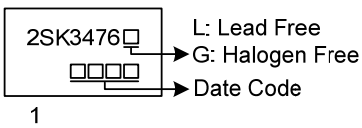
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen-Free		1	2	3	
2SK3476L-AA3-R	2SK3476G-AA3-R	SOT-223	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

2SK3476G-AA3-R (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AA3: SOT-223 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	20	V
Gate- Source Voltage	V_{GSS}	±5	V
Drain Current	I_D	3	A
Power Dissipation (Note 2)	P_D	5	W
Junction Temperature	T_J	+150	°C
Storage Temperature Range	T_{STG}	-45 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. When mounted on a 1.6 mm glass epoxy PCB.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Threshold Voltage	V_{TH}	V_{DS}=7.2V, I_D=2mA	0.55	1.05	1.55	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=20V, V_{GS}=0V			5	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=10V, V_{DS}=0V			5	μA
Drain-source on-voltage	$V_{DS(ON)}$	V_{GS}=10V, I_D=75mA		18		mV
Input capacitance	C_{ISS}	V_{DS}=7.2V, V_{GS}=0V, f=1MHz		53		pF
Output capacitance	C_{OSS}	V_{DS}=7.2V, V_{GS}=0V, f=1MHz		49		pF